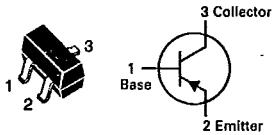


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MOTOROLA SC XSTRS/R F

BSS80BL, CLCASE 318-03, STYLE 6
SOT-23 (TO-236AB)**GENERAL PURPOSE
TRANSISTORS**

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	800	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate,** $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		2.4	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

*FR-5 = $1.0 \times 0.75 \times 0.062$ in.**Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.**DEVICE MARKING**

BSS80BL = CH; BSS80CL = CJ

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10 \text{ mA}$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{A}$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{A}$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}$) ($V_{CB} = 50 \text{ Vdc}, T_A = 150^\circ\text{C}$)	I_{CBO}	—	10 10	nA μA
Emitter Cutoff Current ($V_{BE} = 3.0 \text{ Vdc}$)	I_{EBO}	—	10	nA

ON CHARACTERISTICS

DC Current Gain ($I_C = 150 \text{ mA}, V_{CE} = 10 \text{ Vdc}$)	BSS80BL BSS80CL	h_{FE}	40 100	120 300	—
Collector-Emitter Saturation Voltage ($I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$) ($I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$)	$V_{CE(\text{sat})}$	—	—	0.4 1.6	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 50 \text{ mA}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$)	f_T	200	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, f = 1.0 \text{ MHz}$)	C_{obo}	—	8.0	pF

SWITCHING CHARACTERISTICS

Delay Time	($I_{B1} \approx I_{B2} \approx 15 \text{ mA}$, $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$)	t_d	—	10	ns
Rise Time		t_r	—	40	ns
Storage Time	($I_{B1} \approx I_{B2} \approx 15 \text{ mA}$, $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$)	t_s	—	80	ns
Fall Time		t_f	—	30	ns

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.